

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	804	substrate and channel and impurity and (source or drain or source/drain) and ((stack or stacked or stacking) near5 (gate adj (insulating or dielectric)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:45
L2	100	substrate and channel and impurity and (source or drain or source/drain) and ((stack or stacked or stacking) near5 (gate adj (insulating or dielectric))) and (charge adj storage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:46
L3	39	substrate and channel and impurity and (source or drain or source/drain) and ((stack or stacked or stacking) near5 (gate adj (insulating or dielectric))) and (charge adj storage) and (hot adj electron)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:48
L4	8	substrate and channel and impurity and (source or drain or source/drain) and ((stack or stacked or stacking) near5 (gate adj (insulating or dielectric))) and (charge adj storage) and (hot adj electron) and monos	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:49
L5	1	substrate and channel and impurity and (source or drain or source/drain) and ((stack or stacked or stacking) near5 (gate adj (insulating or dielectric))) and (charge adj storage) and (hot adj electron).clm. and monos	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:49
L6	8	substrate and channel and impurity and (source or drain or source/drain) and ((stack or stacked or stacking) near5 (gate adj (insulating or dielectric))) and (charge adj storage) and (hot adj electron) and monos	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:53
L7	8	substrate and channel and impurity and (source or drain or source/drain) and ((stack or stacked or stacking) near5 (gate adj (insulating or dielectric))) and (charge adj storage) and ((inject or injecting or injected or injection) near5 (hot adj electron)) and monos	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:51

L8	3	substrate and channel and impurity and (source or drain or source/drain) and ((stack or stacked or stacking) near5 (gate adj (insulating or dielectric))).ti, ab,clm. and (charge adj storage) and ((inject or injecting or injected or injection) near5 (hot adj electron)) and monos	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:51
L9	447	((hot adj electron) near5 (inject or injecting or injected or injection)). clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:53
L10	35	((hot adj electron) near5 (inject or injecting or injected or injection)). clm. and (charge adj storage).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:58
L11	6	((hot adj electron) near5 (inject or injecting or injected or injection)). clm. and (charge adj storage).clm. and monos	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:54